8-Input Data Selector/Multiplexer

High-Performance Silicon-Gate CMOS

The MC74HC151 is identical in pinout to the LS151. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device selects one of the eight binary Data Inputs, as determined by the Address Inputs. The Strobe pin must be at a low level for the selected data to appear at the outputs. If Strobe is high, the Y output is forced to a low level and the \overline{Y} output is forced to a high level

The HC151 is similar in function to the HC251 which has 3-state outputs.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

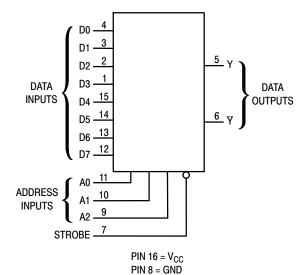
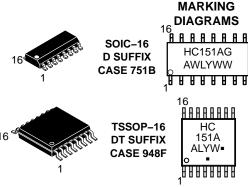


Figure 1. Logic Diagram



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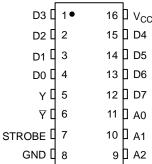


A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



FUNCTION TABLE

	lı	nputs	Out	puts		
A2	A 1	A0	Strobe	Y	Y	
Х	Χ	Χ	Н	L	Н	
L	L	L	L	D0	D0	
L	L	Н	L	D1	D1	
L	Н	L	L	D2	D2	
L	Н	Н	L	D3	D3	
Н	L	L	L	D4	D4	
Н	L	Н	L	D5	D5	
Н	Н	L	L	D6	D6	
Н	Н	Н	L	D7	D7	

D0, D1, ..., D7 = the level of the respective D input.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)		-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)		-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V	
I _{in}	DC Input Current, per Pin	±20	mA	
l _{out}	DC Output Current, per Pin	±25	mA	
Icc	DC Supply Current, V _{CC} and GND Pins		±50	mA
P _D	Power Dissipation in Still Air SOIC Par TSSOP Par	-	500 TBD	mW
T _{stg}	Storage Temperature		-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to	0	V _{CC}	V	
T _A	Operating Temperature, All Package Types	-55	+125	°C	
t _r , t _f	(Figure 2) V _{CC} :	= 2.0 V = 4.5 V = 6.0 V	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

					Guaranteed Limit			
Symbol	Parameter	Test Cond	ditions	v _{cc} v	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CO}$ $ I_{out} \le 20 \mu\text{A}$	_C – 0.1 V	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CO}$ $ I_{out} \le 20 \mu\text{A}$	_C – 0.1 V	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$		2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V _{in} = V _{IH}	$ I_{out} \le 4.0 \text{ mA}$ $ I_{out} \le 5.2 \text{ mA}$	4.5 6.0	3.98 5.48	3.84 5.34	3.70 5.20	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$		2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} = V_{IH}$ or V_{IL}	$ I_{out} \le 4.0 \text{ mA}$ $ I_{out} \le 5.2 \text{ mA}$	4.5 6.0	0.26 0.26	0.33 0.33	0.40 0.40	
l _{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND		6.0	±0.1	±1.0	±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$		6.0	8	80	160	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

			Gu	mit		
Symbol	Parameter	v _{cc}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input D to Output Y (Figures 2 and 7)	2.0 4.5 6.0	170 34 29	215 43 37	255 51 43	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input D to Output ₹ (Figures 4 and 7)	2.0 4.5 6.0	185 37 31	230 46 39	280 56 48	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input D to Output Y (Figures 3 and 7)	2.0 4.5 6.0	185 37 31	230 46 39	280 56 48	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output ₹ (Figures 3 and 7)	2.0 4.5 6.0	205 41 35	255 51 43	310 62 53	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input D to Output Y (Figures 5 and 7)	2.0 4.5 6.0	125 25 21	155 31 26	190 38 32	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Strobe to Output ₹ (Figures 6 and 7)	2.0 4.5 6.0	125 25 21	155 31 26	190 38 32	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2, 4 and 7)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Package)	36	pF

PIN DESCRIPTIONS

INPUTS

D0, D1, ..., D7 (Pins 4, 3, 2, 1, 15, 14, 13, 12)

Data inputs. Data on any one of these eight binary inputs may be selected to appear on the output.

CONTROL INPUTS

A0, A1, A2 (Pins 11, 10, 9)

Address inputs. The data on these pins are the binary address of the selected input (see the Function Table).

Strobe (Pin 7)

Strobe. This input pin must be at a low level for the selected data to appear at the outputs. If the Strobe pin is high, the Y output is forced to a low level and the \overline{Y} output is forced to a high level.

OUTPUTS

Y, \(\overline{Y}\) (Pins 5, 6)

Data outputs. The selected data is presented at these pins in both true (Y output) and complemented (\overline{Y} output) forms.

SWITCHING WAVEFORMS

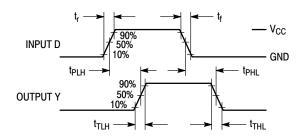


Figure 2.

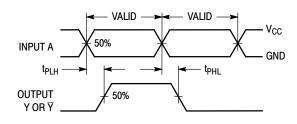


Figure 3.

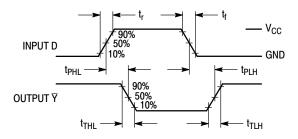


Figure 4.

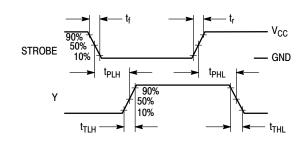


Figure 5.

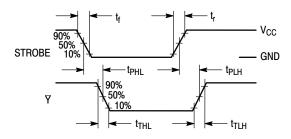
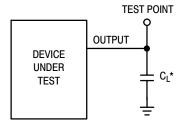


Figure 6.



*Includes all probe and jig capacitance

Figure 7. Test Circuit

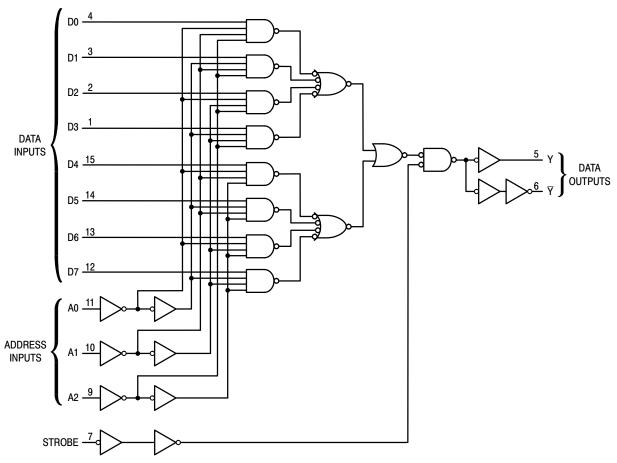


Figure 8. Expanded Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC151ADG		48 Units / Rail
MC74HC151ADR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
NLV74HC151ADR2G*	, ,	2500 Tape & Reel
MC74HC151ADTG		96 Units / Tube
MC74HC151ADTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel
NLV74HC151ADTR2G*		2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.





SOIC-16 CASE 751B-05 **ISSUE K**

DATE 29 DEC 2006

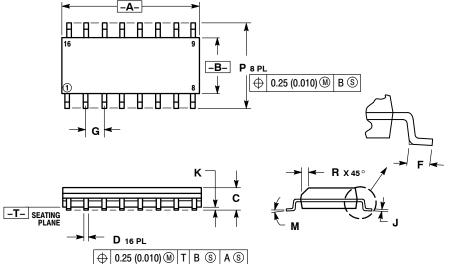
- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD ENGREPHING.
- - PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



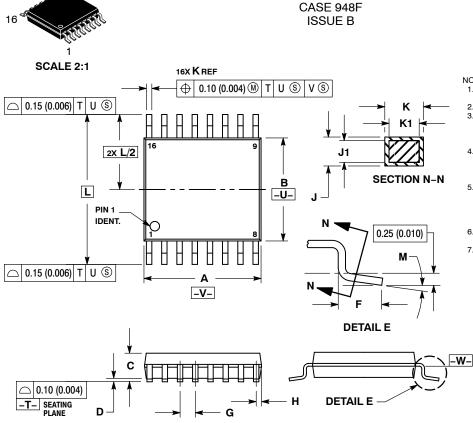
2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION	2. 3. 4. 5. 6. 7. 8. 9. 10.	CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION ANODE CATHODE CATHODE ANODE NO CONNECTION		COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #3 BASE, #3 EMITTER, #3	2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 EMITTER, #4 BASE, #4 BASE, #4 BASE, #3		
12.	EMITTER		CATHODE	12.	COLLECTOR, #3	12.		DECOM	MENDED
13. 14.	BASE COLLECTOR		CATHODE NO CONNECTION	13. 14.	COLLECTOR, #4 BASE, #4	13.	BASE, #2 EMITTER, #2		
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1	SOLDERING	FOOTPRINT*
16.	COLLECTOR		CATHODE	16.	COLLECTOR, #4		EMITTER, #1	g	×
									40
STYLE 5:		STYLE 6:		STYLE 7:				0.	70 7
	DRAIN, DYE #1		CATHODE		SOURCE N-CH			1	ı6X 1.12 < ➤
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPU	T)		<u> </u>	<u> </u>
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPU		1	□ 1	16
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	.,	*	_	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	T)			
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU	T)	16X		
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU	T)	0.58 ^{_1}		
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH			—	
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU		_	<u> </u>	
11.	GATE, #3		ANODE	11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3			12.	COMMON DRAIN (OUTPU	T)			
13.	GATE, #2		ANODE	13.	GATE N-CH				
14.	SOURCE, #2		ANODE	14.	COMMON DRAIN (OUTPU			Ш .	
15.	GATE, #1		ANODE	15.	COMMON DRAIN (OUTPU	T)			PITCH
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH			ш	
								8	9

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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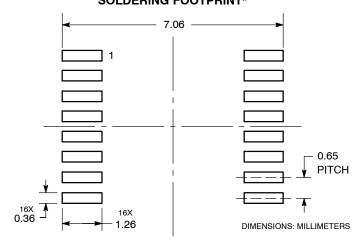
DATE 19 OCT 2006

NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABILE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	٥°	8 °	٥°	8 °	

RECOMMENDED SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week

G or • = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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